

**METHOD AND STRUCTURE FOR FABRICATING A HALF TONE
MASKS FOR THE MANUFACTURE OF SEMICONDUCTOR WAFERS**

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a mask for integrated circuit devices. The method includes providing a quartz substrate having a surface and forming a MoSi film overlying the surface of the quartz substrate. The method also includes patterning the MoSi film overlying the quartz substrate to form a mask pattern. A step of forming an opaque edge structure comprising a carbon bearing material on a portion of the surface around a peripheral region of the mask pattern is also included.

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